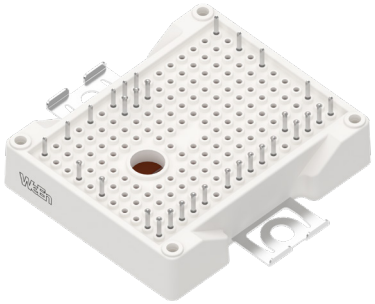
WMG150N06B2S

Module

Rev.01 - 05 January 2024 Preliminary data sheet

1. General description

WMG150N06B2S is a I-type NPC (Neutral Point Clamped) three-level module consisting of two 150A, 650V outer IGBTs with inverse diodes, two 150A, 650V inner IGBTs with inverse diodes, two neutral point 150A, 650 V diodes and an NTC thermistor. The integrated field stop trench IGBTs and FRDs provide lower conduction losses and switching losses, enabling designers to achieve high efficiency and superior reliability.



2. Features and benefits

- I-NPC topology
- Low switching losses
- Low Vcesat
- Compact design
- Solder pin
- Integrated NTC temperature sensor
- Al_2O_3 substrate with low thermal resistance

3. Applications

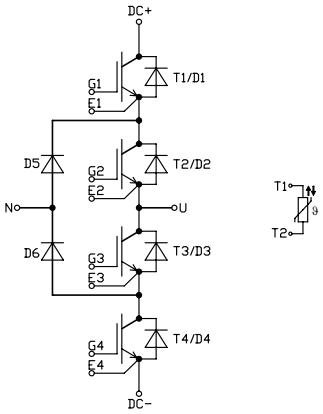
- Three-level applications
- Solar
- Motor Drives
- UPS

4. Ordering information

Table 1. Ordering information

Type number	Package Name	Orderable part number	Packing method	Small packing quantity	Package version	Package issue date
WMG150N06B2S	-	-	-	-	-	-

5. Circuit diagram



6. Limiting values

Table 2. Limiting values

Symbol	Parameter	Test Condition	Value	Unit
Outer IGBT, T1/T4				
V_{CE}	Collector-emitter voltage		650	V
V_{GE}	Gate-emitter voltage		±20	V
I_C	Continous collector current	T_C = 80 °C, limited by T_{jmax}	150	A
I_{Cpulse}	Pulsed collector current	tp limited by T_{jmax}	450	A
P_{tot}	Total power dissipation	T_C = 80 °C	594	W
T_{jmax}	Maximum junction temperature		175	°C
Inner IGBT, T2/T3				
V_{CE}	Collector-emitter voltage		650	V
V_{GE}	Gate-emitter voltage		±20	V
I_C	Continous collector current	T_C = 80 °C, limited by T_{jmax}	150	A
I_{Cpulse}	Pulsed collector current	tp limited by T_{jmax}	450	A
P_{tot}	Total power dissipation	T_C = 80 °C	594	W
T_{jmax}	Maximum junction temperature		175	°C
Neutral Point Diode, D5/D6				
V_{RRM}	Diode repetitive peak reverse voltage		650	V
I_F	Diode Continous collector current	T_C = 80 °C, limited by T_{jmax}	150	A
I_{FRM}	Diode repetitive reak forward current	tp limited by T_{jmax}	450	A
P_{tot}	Total power dissipation	T_C = 80 °C	257	W
T_{jmax}	Maximum junction temperature		175	°C
Inverse Diode, D1/D2/D3/D4				
V_{RRM}	Diode repetitive peak reverse voltage		650	V
I_F	Diode Continous collector current	T_C = 80 °C, limited by T_{jmax}	150	A
I_{FRM}	Diode repetitive reak forward current	tp limited by T_{jmax}	450	A
P_{tot}	Total power dissipation	T_C = 80 °C	257	W
T_{jmax}	Maximum junction temperature		175	°C

7. Module package thermal & insulation

Table 3. Thermal & Insulation properties

Symbol	Parameter	Test Condition	Value	Unit
V_{ISOL}	RMS isolation voltage	T_j = 25 °C, all terminals shorted, f = 50 Hz, t = 1 min	2500	V
d_{Creep}	Creepage distance	terminal to heatsink	11.5	mm
d_{Clear}	Clearance	terminal to heatsink	10	mm
CTI	Comperative tracking index		> 200	
T_{stg}	Storage temperature		-40 to 125	°C

8. Electrical characteristics

Table 4. Characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Outer IGBT characteristics, T1/T4						
V_{CEsat}	Collector-emitter saturation voltage	V_{GE} = 15 V; I_C = 150 A; T_j = 25 °C	-	1.6	-	V
		V_{GE} = 15 V; I_C = 150 A; T_j = 150 °C	-	2.0	-	V
$V_{GE(th)}$	Gate-emitter threhold voltage	I_C = 1.5 mA; V_{CE} = V_{GE}; T_j = 25 °C	4.3	5.4	6.5	V
I_{CES}	Zero gate voltage collector current	V_{CE} = 650 V; V_{GE} = 0 V; T_j = 25 °C	-	-	10	µA
I_{GES}	Gate leakage current	V_{GE} = 20 V; V_{CE} = 0 V; T_j = 25 °C	-	-	100	nA
Q_G	Gate charge	V_{CC} = 300 V; I_C = 150 A; V_{GE} = ±15 V	-	606	-	nC
C_{ies}	Input capacitance	V_{CE} = 25 V; V_{GE} = 0V; f = 1 MHz; T_j = 25 °C	-	8880	-	pF
C_{oes}	Output capacitance		-	587	-	pF
C_{res}	Reverse transfer capacitance		-	150	-	pF
$t_{d(on)}$	Turn-on delay time	T_j = 25 °C V_{CC} = 300 V; I_C = 150 A; V_{GE} = ±15 V; R_g = 10 Ω	-	42	-	nS
t_r	Rise time		-	35	-	nS
$t_{d(off)}$	Turn-off delay time		-	155	-	nS
t_f	Fall time		-	60	-	nS
E_{on}	Turn-on energy		-	2.3	-	mJ
E_{off}	Turn-off energy		-	1.8	-	mJ
$t_{d(on)}$	Turn-on delay time	T_j =150 °C V_{CC} = 300 V; I_C = 150 A; V_{GE} = ±15 V; R_g = 10 Ω	-	38	-	nS
t_r	Rise time		-	40	-	nS
$t_{d(off)}$	Turn-off delay time		-	164	-	nS
t_f	Fall time		-	83	-	nS
E_{on}	Turn-on energy		-	3.6	-	mJ
E_{off}	Turn-off energy		-	2.4	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.16	-	K/W
T_{jop}	Operation temperature		-40		150	°C
Neutral point Diode characteristics, D5/D6						
V_F	Diode forward voltage	I_F = 150 A; T_j = 25 °C	-	1.75	-	V
		I_F = 150 A; T_j = 150 °C	-	1.5	-	V
Q_{rr}	Reverse recovery charge	T_j = 25 °C V_R = 300 V; I_F = 150 A; di/dt = 2300 A/µs;	-	1113	-	nC
I_{rrm}	Peak reverse recovery current		-	51	-	A
E_{rr}	Reverse recovery energy		-	0.2	-	mJ
Q_{rr}	Reverse recovery charge	T_j = 150 °C V_R = 300 V; I_F = 150 A; di/dt = 2000 A/µs;	-	4711	-	nC
I_{rrm}	Peak reverse recovery current		-	71	-	A
E_{rr}	Reverse recovery energy		-	0.82	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.37	-	K/W
T_{jop}	Operation temperature		-40		150	°C

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Inner IGBT characteristics, T2/T3						
V_{CEsat}	Collector-emitter saturation voltage	V_{GE} = 15 V; I_C = 150 A; T_j = 25 °C	-	1.6	-	V
		V_{GE} = 15 V; I_C = 150 A; T_j = 150 °C	-	2.0	-	V
$V_{GE(th)}$	Gate-emitter threhold voltage	I_C = 1.5 mA; V_{CE} = V_{GE}; T_j = 25 °C	4.3	5.4	6.5	V
I_{CES}	Zero gate voltage collector current	V_{CE} = 650 V; V_{GE} = 0 V; T_j = 25 °C	-	-	10	μA
I_{GES}	Gate leakage current	V_{GE} = 20 V; V_{CE} = 0 V; T_j = 25 °C	-	-	100	nA
Q_G	Gate charge	V_{CC} = 300 V; I_C = 150 A; V_{GE} = ±15 V	-	606	-	nC
C_{ies}	Input capacitance	V_{CE} = 25 V; V_{GE} = 0V; f = 1 MHz; T_j = 25 °C	-	8880	-	pF
C_{oes}	Output capacitance		-	587	-	pF
C_{res}	Reverse transfer capacitance		-	150	-	pF
$t_{d(on)}$	Turn-on delay time	T_j = 25 °C V_{CC} = 300 V; I_C = 150 A; V_{GE} = ±15 V; R_g = 10 Ω	-	41	-	nS
t_r	Rise time		-	27	-	nS
$t_{d(off)}$	Turn-off delay time		-	150	-	nS
t_f	Fall time		-	46	-	nS
E_{on}	Turn-on energy		-	1.5	-	mJ
E_{off}	Turn-off energy		-	1.8	-	mJ
$t_{d(on)}$	Turn-on delay time	T_j =150 °C V_{CC} = 300 V; I_C = 150 A; V_{GE} = ±15 V; R_g = 10 Ω	-	38	-	nS
t_r	Rise time		-	32	-	nS
$t_{d(off)}$	Turn-off delay time		-	163	-	nS
t_f	Fall time		-	72	-	nS
E_{on}	Turn-on energy		-	2.7	-	mJ
E_{off}	Turn-off energy		-	2.4	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.16	-	K/W
T_{jop}	Operation temperature		-40		150	°C
Inverter Diode characteristics, D1/D2/D3/D4						
V_F	Diode forward voltage	I_F = 150 A; T_j = 25 °C	-	1.75	-	V
		I_F = 150 A; T_j = 150 °C	-	1.5	-	V
Q_{rr}	Reverse recovery charge	T_j = 25 °C V_R = 300 V; I_F = 150 A; di/dt = 3600 A/μs;	-	1464	-	nC
I_{rrm}	Peak reverse recovery current		-	71	-	A
E_{rr}	Reverse recovery energy		-	0.3	-	mJ
Q_{rr}	Reverse recovery charge	T_j = 150 °C V_R = 300 V; I_F = 150 A; di/dt = 3000 A/μs;	-	5520	-	nC
I_{rrm}	Peak reverse recovery current		-	75	-	A
E_{rr}	Reverse recovery energy		-	1.1	-	mJ
R_{thJC}	Thermal resistance, junction to case		-	0.37	-	K/W
T_{jop}	Operation temperature		-40		150	°C

9. NTC - thermistor

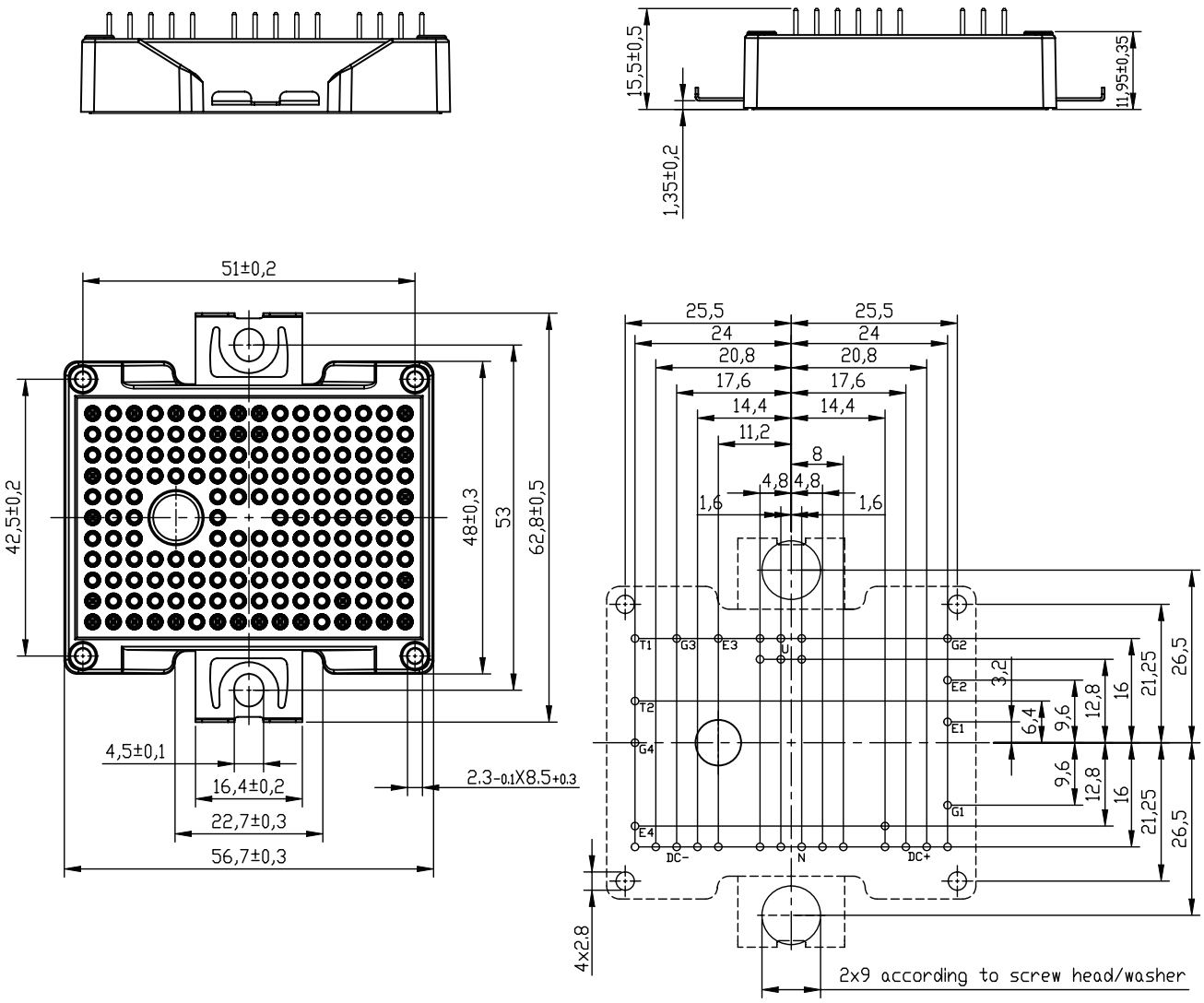
Table 5. NTC - Thermistor

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
R_{25}	Rated resistance	T_c = 25 °C	-	5000	-	Ω
R_{100}		T_c = 100 °C	465±5%			Ω
$B_{25/50}$	B-value	$R_2=R_{25}$ exp.[$B_{25/50}$(1/T_2-1(298.15K))]	3380±5%			K

10. Package outline

WeEnPACK-B2PTL-B

Package Outline



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Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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12. Contents

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Date of release: 05 January 2024